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Vishay/Siliconix SQM200N04-1M7L-GE3

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### SQM200N04-1m7L

Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0017				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0020				
I <sub>D</sub> (A)	200				
Configuration	Single				
Package	TO-263-7L				

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#### **FEATURES**

TrenchFET® power MOSFET

N-Channel MOSFET

- Package with low thermal resistance
- 100 % R<sub>q</sub> and UIS tested
- AEC-Q101 qualified <sup>d</sup>
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ABSOLUTE MAXIMUM RATIN	(1) = 25 O, unless				
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	40	V	
Gate-Source Voltage		$V_{GS}$	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	I <sub>D</sub>	200		
Continuous Drain Current	T <sub>C</sub> = 125 °C		193		
Continuous Source Current (Diode Conduc	ction) <sup>a</sup>	I <sub>S</sub>	200	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	600		
Single Pulse Avalanche Current		I <sub>AS</sub>	95		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	451	mJ	
Manipular Device Dispiration h	T <sub>C</sub> = 25 °C	D	375	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	125	]	
Operating Junction and Storage Temperat	ure Range	T <sub>J</sub> , T <sub>stq</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount c	$R_{thJA}$	40	°C/W		
Junction-to-Case (Drain)		$R_{thJC}$	0.4	C/VV		

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

Datasheet of SQM200N04-1M7L-GE3 - MOSFET N-CH 40V 200A TO-263

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		40	-	-		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		2.0	2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
-		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	200	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.0012	0.0017	Ω	
Dunin Course On State Perintense 3		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0028		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0034		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 20 A	-	0.0014	0.0020		
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		-	181	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 20 V, f = 1 MHz	-	8934	11 168	pF	
Output Capacitance	Coss	$V_{GS} = 0 V$		-	1592	1990		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	928	1160		
Total Gate Charge <sup>c</sup>	Qg			-	194	291		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_{D} = 20 \text{ A}$	-	25	-	nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	]		-	40	-	-	
Gate Resistance	$R_g$	f = 1 MHz		0.25	0.8	1.8	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_L = 1 \Omega$ $I_D \cong 20 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	22	33	- ns	
Rise Time <sup>c</sup>	t <sub>r</sub>			-	17	26		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	70	105		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	16	24		
Source-Drain Diode Ratings and Characteristics <sup>b</sup>								
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	600	Α	
Forward Voltage	$V_{SD}$	$I_F = 60 \text{ A}, V_{GS} = 0 \text{ V}$		-	0.8	1.5	V	

#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Datasheet of SQM200N04-1M7L-GE3 - MOSFET N-CH 40V 200A TO-263 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

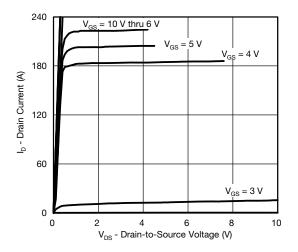
# SQM200N04-1m7L



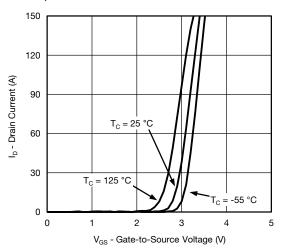
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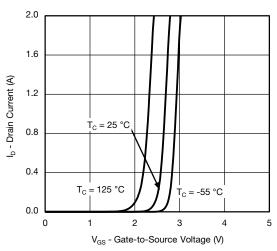
#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



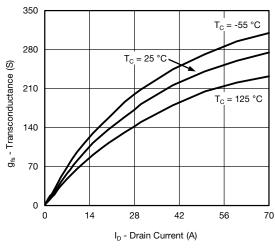
#### **Output Characteristics**



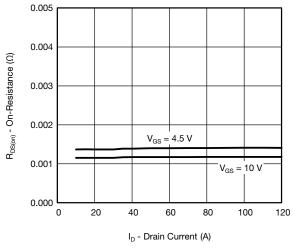
**Transfer Characteristics** 



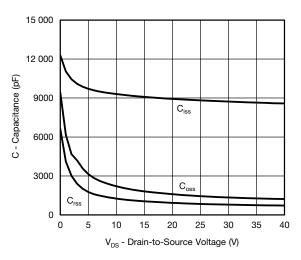
Transfer Characteristics



Transconductance



On-Resistance vs. Drain Current



Capacitance

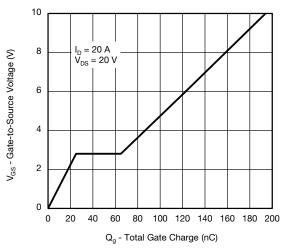




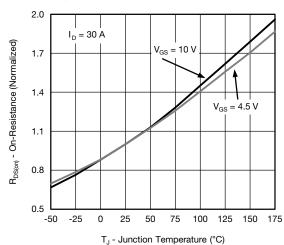
### SQM200N04-1m7L

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#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

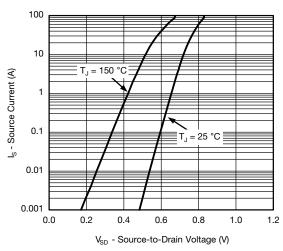


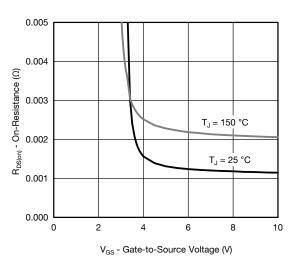
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#### **Gate Charge**

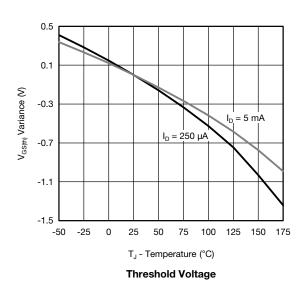
On-Resistance vs. Junction Temperature

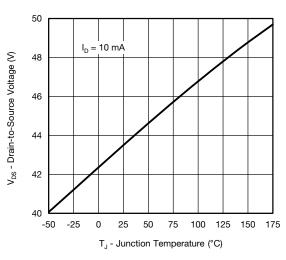




Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage





Drain Source Breakdown vs. Junction Temperature

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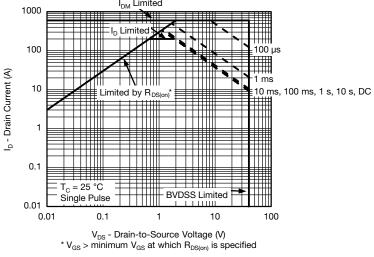
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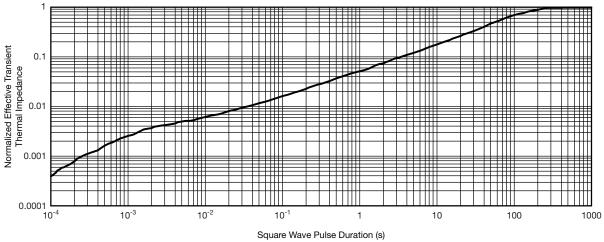
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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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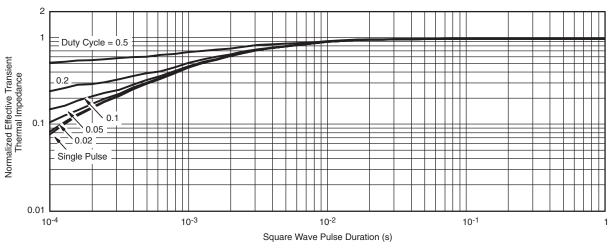


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**THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

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Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?67058">www.vishay.com/ppg?67058</a>.



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REVISION HISTORY <sup>a</sup>				
REVISION	DATE	DESCRIPTION OF CHANGE		
В	04-Aug-15	Revised R <sub>g</sub> minimum limit		

#### Note

a. As of April 2014

Datasheet of SQM200N04-1M7L-GE3 - MOSFET N-CH 40V 200A TO-263

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# **Ordering Information**

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# D<sup>2</sup>PAK / TO-263 and TO-262

Ordering codes for the SQ rugged series power MOSFETs in the D2PAK / TO-263 and TO-262 packages:

DATASHEET PART NUMBER	OLD ORDERING CODE a	NEW ORDERING CODE
SQM100N04-2m7	SQM100N04-2M7-GE3	SQM100N04-2M7_GE3
SQM100N10-10	SQM100N10-10-GE3	SQM100N10-10_GE3
SQM110N05-06L	SQM110N05-06L-GE3	SQM110N05-06L_GE3
SQM110P06-8m9L	SQM110P06-8M9L-GE3	SQM110P06-8M9L_GE3
SQM120N02-1m3L	SQM120N02-1M3L-GE3	SQM120N02-1M3L_GE3
SQM120N03-1m5L	SQM120N03-1M5L-GE3	SQM120N03-1M5L_GE3
SQM120N04-1m7	SQM120N04-1M7-GE3	SQM120N04-1M7_GE3
SQM120N04-1m7L	SQM120N04-1M7L-GE3	SQM120N04-1M7L_GE3
SQM120N04-1m9	SQM120N04-1M9-GE3	SQM120N04-1M9_GE3
SQM120N06-06	SQM120N06-06-GE3	SQM120N06-06_GE3
SQM120N06-3m5L	SQM120N06-3M5L-GE3	SQM120N06-3M5L_GE3
SQM120N10-09	SQM120N10-09-GE3	SQM120N10-09_GE3
SQM120N10-3m8	SQM120N10-3M8-GE3	SQM120N10-3M8_GE3
SQM120P04-04L	SQM120P04-04L-GE3	SQM120P04-04L_GE3
SQM120P06-07L	SQM120P06-07L-GE3	SQM120P06-07L_GE3
SQM120P10-10m1L	-	SQM120P10_10m1LGE3
SQM200N04-1m1L	SQM200N04-1M1L-GE3	SQM200N04-1M1L_GE3
SQM200N04-1m7L	SQM200N04-1M7L-GE3	SQM200N04-1M7L_GE3
SQM200N04-1m8	SQM200N04-1M8-GE3	SQM200N04-1M8_GE3
SQM25N15-52	SQM25N15-52-GE3	SQM25N15-52_GE3
SQM35N30-97	SQM35N30-97-GE3	SQM35N30-97_GE3
SQM40010EL	-	SQM40010EL_GE3
SQM40N10-30	SQM40N10-30-GE3	SQM40N10-30_GE3
SQM40N15-38	SQM40N15-38-GE3	SQM40N15-38_GE3
SQM40P10-40L	SQM40P10-40L-GE3	SQM40P10-40L_GE3
SQM47N10-24L	SQM47N10-24L-GE3	SQM47N10-24L_GE3
SQM50020EL	-	SQM50020EL_GE3
SQM50N04-4m0L	SQM50N04-4M0L-GE3	SQM50N04-4M0L_GE3
SQM50N04-4m1	SQM50N04-4M1-GE3	SQM50N04-4M1_GE3
SQM50P03-07	SQM50P03-07-GE3	SQM50P03-07_GE3
SQM50P04-09L	SQM50P04-09L-GE3	SQM50P04-09L_GE3
SQM50P06-15L	SQM50P06-15L-GE3	SQM50P06-15L_GE3
SQM50P08-25L	SQM50P08-25L-GE3	SQM50P08-25L_GE3
SQM60030E	-	SQM60030E_GE3
SQM60N06-15	SQM60N06-15-GE3	SQM60N06-15_GE3
SQM60N20-35	SQM60N20-35-GE3	SQM60N20-35_GE3
SQM70060EL	-	SQM70060EL_GE3
SQM85N15-19	SQM85N15-19-GE3	SQM85N15-19_GE3
SQV120N10-3m8	SQV120N10-3m8-GE3	SQV120N10-3m8_GE3
SQV120N06-4m7L	-	SQV120N06-4m7L GE3

#### Note

Revision: 06-Jul-16 1 Document Number: 67164

a. Old ordering code is obsolete and no longer valid for new orders

Datasheet of SQM200N04-1M7L-GE3 - MOSFET N-CH 40V 200A TO-263

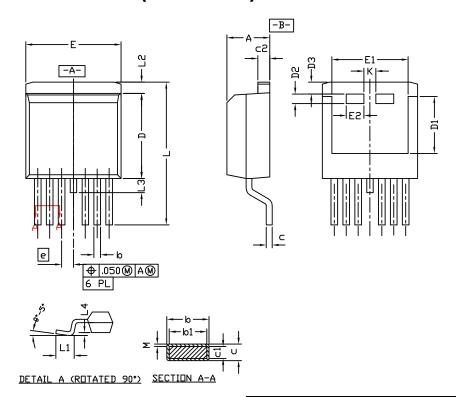
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# D<sup>2</sup>PAK (TO-263-7L) Case Outline



#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

	INCHES		MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050	BSC	1.27 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
М	-	0.002	-	0.050	
ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006					

Revision: 30-Sep-13 Document Number: 63782



Datasheet of SQM200N04-1M7L-GE3 - MOSFET N-CH 40V 200A TO-263

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Revision: 13-Jun-16 Document Number: 91000 1